

MV4320

KEYPAD PULSE DIALLER

The MV4320 is fabricated using ISO-CMOS high density technology. The device is a pin-for-pin replacement for the DF320 Loop Disconnect Dialler and offers wider operating supply voltage range and lower power dissipation. The MV4320 accepts up to 20 digits from a standard 2 of 7 keypad and has a REDIAL option which is activated by the # key. The device provides dial pulsing and muting outputs and has a HOLD pin for interrupting a dialling sequence. Outpulsing, mark/space ratio and dialling speed are pin selectable.

The MV4320 is available in Ceramic DIL (DG, -40°C to +85°C).

FEATURES

- Pin for Pin Replacement for the DF320
- 2.5V to 5.5V Supply Voltage Operating Range
- 375 μ W Dynamic Power Dissipation at 3V
- Uses Inexpensive 3.58 MHz Ceramic Resonator or Crystal
- Stores up to 20 Digits
- Selectable Outpulsing Mark/Space Ratio
- Selectable Dialling Speeds of 10, 16, 20 and 932 Hz
- Low Cost

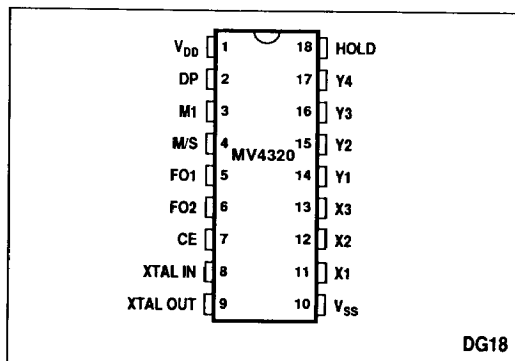


Fig.1 Pin connections - top view

APPLICATIONS

- Pushbutton Telephones
- Tone to Pulse Converters
- Mobile Telephone
- Repertory Dialers

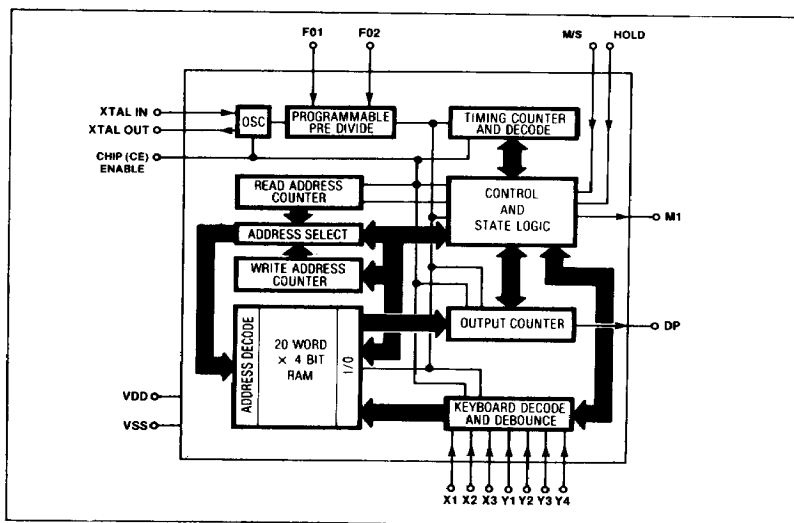


Fig.2 MV4320 functional block diagram

DC ELECTRICAL CHARACTERISTICS**Test conditions (unless otherwise stated):**

$V_{DD} = 3.0V$; $T_{amb} = +25^{\circ}C$; $f_{CLK} = 3.579545\text{ MHz}$

All voltages wrt V_{SS}

	CHARACTERISTICS		SYMBOL	MIN	TYP*	MAX	UNITS	TEST CONDITIONS	
1	SUPPLY	Supply Voltage Operating Range	V_{DD}	2.5		5.5	V		
2		Standby Supply Current	I_{DDS}		1.0	10.0	μA	$CE = V_{SS}$	
3		Operating Supply Current	I_{DD}		125	200	μA	3.579545 MHz Crystal, $C_{XTALOUT} = 12\text{ pF}$	
4	INPUT	Pull-Up Transistor Source Current	I_{IL}	-0.5	-3.0	-12.0	μA	$V_{IN} = V_{SS}$	X_1, X_2, X_3
5		Input Leakage Current	I_{IH}		0.1		nA	$V_{IN} = V_{DD}$	Y_1, Y_2, Y_3, Y_4
6		Input Leakage Current	I_{IL}		-0.1		nA	$V_{IN} = V_{SS}$	M/S, IDP, F01,
7		Pull-Down Transistor Sink Current	I_{IH}	0.5	3.0	12.0	μA	$V_{IN} = V_{DD}$	F02, FD, HOLD
8		Logic '0' Level	V_{IL}			0.9	V	All inputs	
9		Logic '1' Level	V_{IH}	2.1			V		
10	OUTPUT	Voltage Levels	Low-Level	V_{OL}		0	0.01	V	No Load
11			High-level	V_{OH}	2.99	3		V	DP, M1/M2
12		Drive Current	N-Channel Sink	I_{OL}	0.8	2.0		mA	
13			P-Channel Source	I_{OH}	-0.8	-2.0		mA	

AC ELECTRICAL CHARACTERISTICS**Test conditions (unless otherwise stated):**

$V_{DD} = 3.0V$; $T_{amb} = +25^{\circ}C$; $f_{CLK} = 3.579545\text{ MHz}$

All voltages wrt V_{SS}

	CHARACTERISTICS		SYMBOL	MIN	TYP*	MAX	UNITS	TEST CONDITIONS	
14	DYNAMIC	Output Rise Time	t_R		1.0		μs	DP, M1.	
15		Output Fall Time	t_F		1.0		μs	$C_L = 50\text{ pF}$	
16		Maximum Clock Frequency	f_{CLK}	3.58			MHz	3.579545 MHz Crystal	
17		Mark to Space Ratio	M/S		2:1			Note 1	
18					3:2				
19		Impulsing Rate = $\frac{1}{T}$			10		Hz	Note 1	
20					16				
21					20				
22					932				
23		Clock Start Up Time	t_{on}		1.5	4	ms	Timed from CE '1'	
24		Input Capacitance	C_{in}		5.0		pF	Any Input	

* Typical parametric values are for Design Aid Only, not guaranteed and not subject to production testing. Timing waveforms are subject to production functional test.

NOTES:

1. See Pin Function, Table 1.

OPERATING NOTES

The first key entered in any dialling sequence initiates the oscillator by internally taking CE high. Digits may be entered asynchronously from the keypad. Dialling and mute functions are output as shown in figures 3 and 4. Figure 3 shows use of the circuits with external control of CE. This mode is useful if a bistable latching relay is used to mute and switch the complete pulse dialler circuit. In

this mode, the pulse occurring on M1 when CE is taken high, with no keypad input, can be used to initiate the bistable latching relay. Figure 4 shows the timing diagram for the CE internal control mode. Initially CE is low and goes high on recognition of the first valid key input. Keypad data is entered asynchronously.

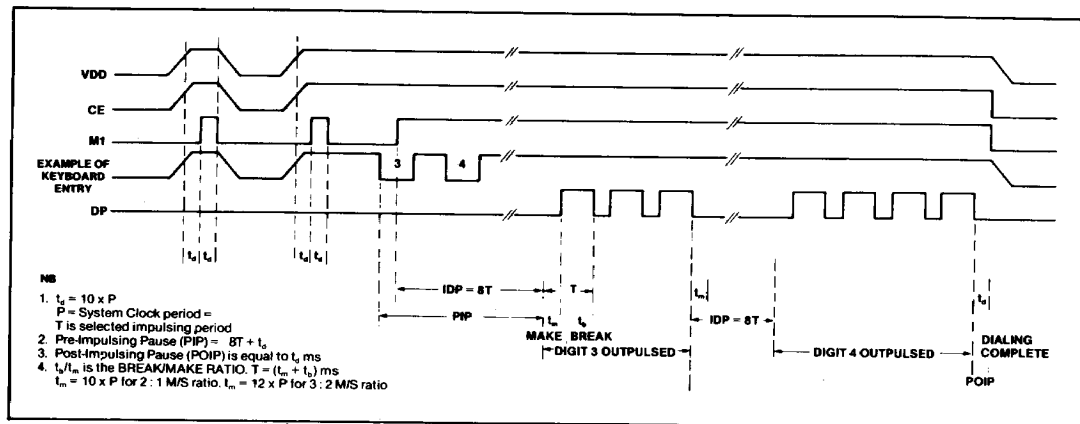


Fig.3 Keypad pulse dialer timing diagram, CE-External control

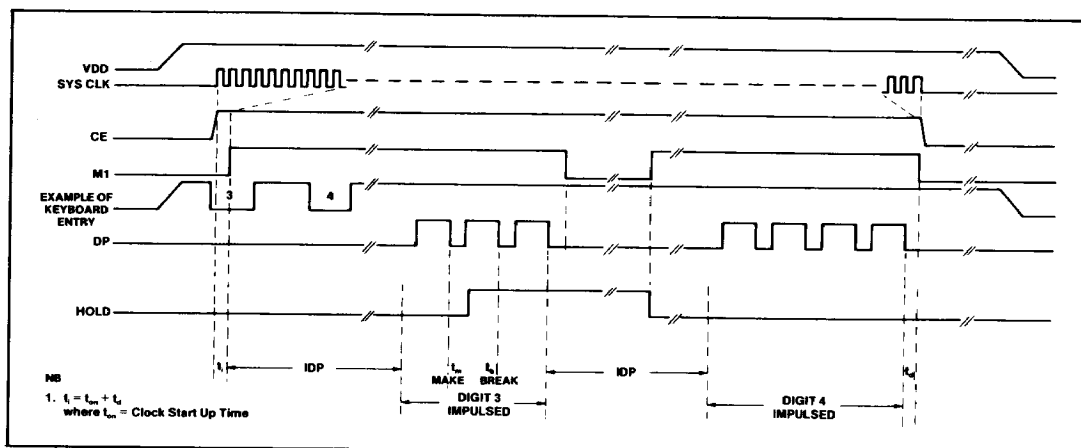


Fig.4 Keypad pulse dialer timing diagram, CE-Internal control

ABSOLUTE MAXIMUM RATINGS

The absolute maximum ratings are limiting values above which operating life may be shortened or specified parameters may be degraded.

	MIN.	MAX.
$V_{DD}-V_{SS}$	-0.3V	10V
Voltage on any pin	$V_{SS} - 0.3V$	$V_{DD} + 0.3V$
Current at any pin		10mA
Operating Temperature	-40°C	+85°C
Storage Temperature	-65°C	+150°C
Power Dissipation		1000mW
Derate 16mW/°C above 75°C. All leads soldered to PC board.		

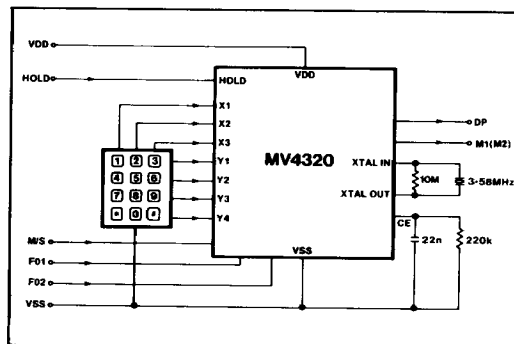


Fig.5 Application diagram

PIN FUNCTIONS

VDD	Positive voltage supply					
DP	Dial Pulsing Output Buffer					
M1	Mute Output (Off Normal) Buffer					
M/S	Mark/Space (Break/Make) Ratio select. On-chip pull-down transistor to VSS.				O/C	2:1
	Note: O/C = Open Circuit				VDD	3:2
F01,F02	Impulsing Rate Selection. On-chip pull-down transistor to VSS. * Assumes fCLK = 3.579545MHz.	F01	F02	Nominal Impulsing Rate	Actual* Impulsing Rate	System Clock frequency
		O/C	O/C	10Hz	10.13Hz	303.9Hz
		O/C	VDD	20Hz	19.42Hz	582.6Hz
		VDD	O/C	932Hz	932.17Hz	27,965.1Hz
		VDD	VDD	16Hz	15.54Hz	466.1Hz
CE	Chip Enable. An active input. Control is internal via static keyboard decode, or by external forcing.					
XTAL IN	Crystal Input. Active, clamped low if CE = '0', high impedance if CE = '1'.					
XTAL OUT	Crystal Output Buffer to drive crystal.					
VSS	System ground					
X1,X2,X3	Column keyboard Inputs. On-chip pull-up transistors to VDD. Active LOW.					
Y1,Y2,Y3,Y4	Row keyboard Inputs. On-chip pull-up transistors to VDD. Active LOW.					
HOLD		O/C	Normal Operation			
		VDD	No impulsing. If activated during impulsing, hold occurs when the current digit is complete			
	Prevents further impulsing. On-chip pull-down transistor to VSS.					